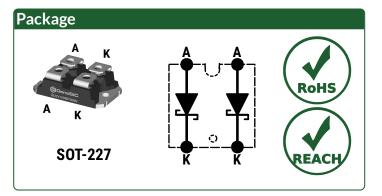
GeneSiC SEMICONDUCTOR

Silicon Carbide Schottky Diode

 V_{RRM} = 650 V $I_{F(T_C = 86^{\circ}C)}$ = 200 A * Q_C = 308 nC *

Features

- Gen4 Thin Chip Technology for Low V_F
- Superior Figure of Merit Q_C/I_F
- 100% Avalanche Tested
- Enhanced Surge Current Robustness
- Temperature Independent Fast Switching
- Low Thermal Resistance
- Positive Temperature Coefficient of V_F
- High dV/dt Ruggedness



Advantages

- Optimal Price Performance
- Improved System Efficiency
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- High System Reliability
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

Applications

- EV Fast Chargers
- Solar Inverters
- Switched Mode Power Supply (SMPS)
- High frequency Converters
- Motor Drives
- Induction Heating and Welding
- Uninterruptible Power Supply (UPS)
- Pulsed Power

Absolute Maximum Ratings (At T _C = 25°C Unless Otherwise Stated)										
Parameter	Symbol	Conditions	Values	Unit	Note					
Repetitive Peak Reverse Voltage (Per Leg)	V_{RRM}		650	٧						
Continuous Forward Current (Per Leg / Per Device)	IF	$T_C = 75^{\circ}C$, D = 1	108 / 216							
		$T_C = 100^{\circ}C, D = 1$	90 / 180	Α	Fig. 4					
		$T_C = 86^{\circ}C, D = 1$	100 / 200	0 / 200						
Non-Repetitive Peak Forward Surge Current, Half Sine Wave (Per Leg)	I _{F,SM}	T_C = 25°C, t_P = 10 ms	550	Α						
		T_C = 150°C, t_P = 10 ms	440							
Repetitive Peak Forward Surge Current, Half Sine Wave	lenu	T_C = 25°C, t_P = 10 ms	330	А						
(Per Leg)	I _{F,RM}	T_C = 150°C, t_P = 10 ms	231							
Non-Repetitive Peak Forward Surge Current (Per Leg)	I _{F,MAX}	T_C = 25°C, t_P = 10 μ s	2750	Α						
i²t Value (Per Leg)	∫i²dt	$T_C = 25^{\circ}C$, $t_P = 10 \text{ ms}$	1512	A ² s						
Non-Repetitive Avalanche Energy (Per Leg)	E _{AS}	L = 0.2 mH, I _{AS} = 100 A	920	mJ						
Diode Ruggedness (Per Leg)	dV/dt	$V_R = 0 \sim 520 \text{ V}$	200	V/ns						
Power Dissipation (Per Leg / Per Device)	P _{TOT}	T _C = 25°C	301 / 602	W	Fig. 3					
Operating and Storage Temperature	T_j , T_{stg}		-55 to 175	°C						

^{*} Per Device





Electrical Characteristics (Per Leg) Values **Parameter Symbol Conditions** Unit Note Min. Тур. Max. $I_F = 100 A$, $T_i = 25$ °C 1.5 1.8 ٧ Diode Forward Voltage V_{F} Fig. 1 $I_F = 100 \text{ A}, T_j = 175^{\circ}\text{C}$ 1.8 $V_R = 650 \text{ V, } T_i = 25^{\circ}\text{C}$ 5 1 **Reverse Current** Fig. 2 I_R μΑ $V_R = 650 \text{ V}, T_i = 175^{\circ}\text{C}$ 18 $V_R = 200 V$ 105 **Total Capacitive Charge** $Q_{\mathbb{C}}$ nC Fig. 7 $V_R = 400 V$ 154 $I_F \leq I_{F,MAX}$ $dI_F/dt = 200 A/\mu s$ $V_R = 200 V$ Switching Time < 10 ts ns $V_R = 400 V$ $V_R = 1 V$, f = 1MHz2450 С **Total Capacitance** рF Fig. 6 V_R = 400 V, f = 1MHz 210

Thermal/Package Characteristics										
Parameter	Symbol	Conditions	Values			- Unit	Note			
			Min.	Тур.	Max.	Ullit	Note			
Thermal Resistance, Junction - Case (Per Leg)	RthJC			0.5		°C/W	Fig. 9			
Weight	W _T			28.0		g				
Mounting Torque	T _M	Screws to Heatsink			1.5	Nm				
Terminal Connection Torque	Tc	M4 Screws			1.3	Nm				
Isolation Voltage(RMS)	V _{ISO}	t = 1s (50/60 Hz)		3000		V				
		t = 60s (50/60 Hz)		2500		V				
Creepage Distance on Surface	dctt	Terminal to Terminal		10.5						
	dctb	Terminal to Backside		8.5		mm				
Striking Distance Through Air	dstt	Terminal to Terminal		3.2						
	d_{Stb}	Terminal to Backside		6.8		mm				





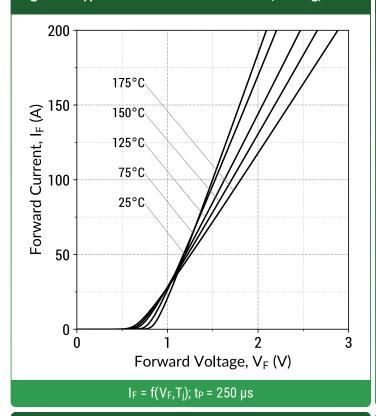


Figure 2: Typical Reverse Characteristics (Per Leg)

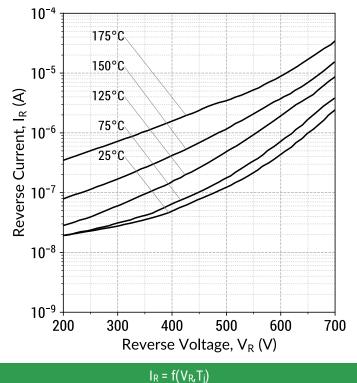


Figure 3: Power Derating Curves (Per Leg)

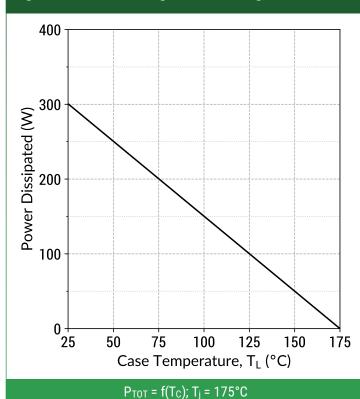
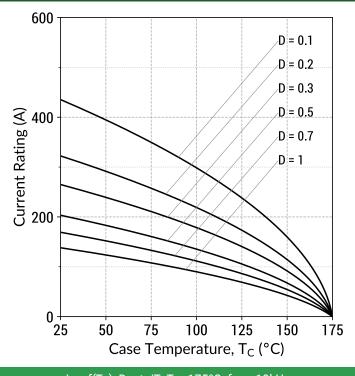


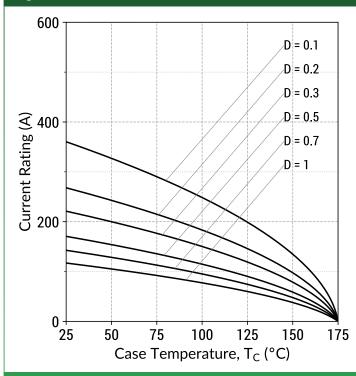
Figure 4: Current Derating Curves (Typical V_F) (Per Leg)



 $I_F = f(T_C)$; D = t_P/T ; $T_j \le 175$ °C; $f_{SW} > 10$ kHz

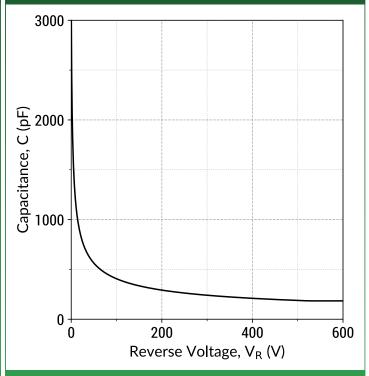


Figure 5: Current Derating Curves (Maximum V_F) (Per Leg)



 $I_F = f(T_C); D = t_P/T; T_i \le 175^{\circ}C; f_{SW} > 10kHz$

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics (Per Leg)



 $C = f(V_R)$; f = 1MHz

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics (Per Leg)

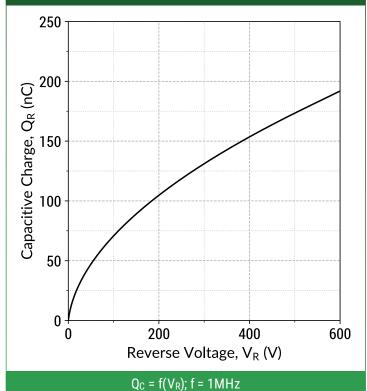
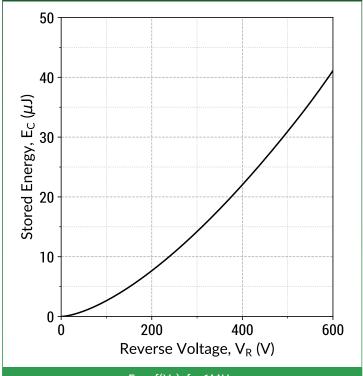


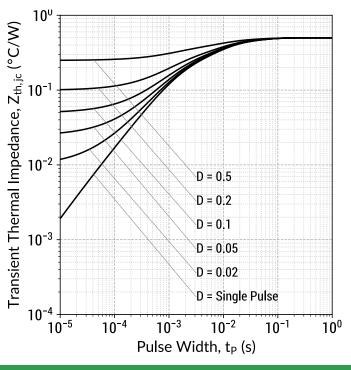
Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics (Per Leg)



 $E_C = f(V_R)$; f = 1MHz

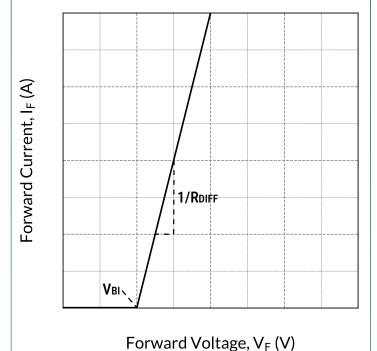


Figure 9: Transient Thermal Impedance (Per Leg)



 $Z_{th,jc} = f(t_P,D); D = t_P/T$

Figure 10: Forward Curve Model (Per Leg)



 $I_F = f(V_F, T_j)$

Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF}(A)$

Built-In Voltage (V_{BI}):

 $V_{BI}(T_j) = m \times T_j + n (V)$ $m = -0.00115 (V/^{\circ}C)$ n = 9.31e-01 (V)

Differential Resistance (RDIFF):

 $R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$ $a = 1.52e-07 (\Omega/^{\circ}C^2)$ $b = 1.65e-06 (\Omega/^{\circ}C)$ $c = 0.00583 (\Omega)$

Forward Power Loss Equation:

 $P_{LOSS} = V_{BI}(T_j) \times I_{AVG} + R_{DIFF}(T_j) \times I_{RMS}^2$



Package Dimensions SOT-227 Package Outline 0.472 (11.9) 0.480 (12.19) 1.240 (31.5) 1.255 (31.88) 0.372 (9.45) 0.108 (2.74) 0.124 (3.15) 0.310 (7.87) 0.322 (8.18) Ø <u>0.163 (4.14)</u> 0.169 (4.29) R 3.97 1.049 (26.6) 1.059 (26.90) 0.163 (4.14) 0.169 (4.29) 0.990 (25.1) 1.000 (25.40) 0.495 (12.5) 0.506 (12.85) 0.172 (4.37) 0.186 (4.72) 0.191 (4.85) 0.080 (2.03) 0.234 (5.94) 0.084 (2.13) 0.165 (4.19) 0.169 (4.29) 0.030 (0.76) 0.033 (0.84) 0.588 (14.9) 0.594 (15.09) 1.186 (30.1) 1.192 (30.28) 1.494 (37.9) 1.504 (38.20) Package View **Isolated Base**

NOTE

- 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.





Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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 Quality Manual: https://www.genesicsemi.com/quality

Revision History

• Rev 21/Mar: Updated with most recent data

· Supersedes: Rev 20/Jul



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